

In the Specification:

Please amend the first full paragraph on page 5 as follows:

Exemplary embodiments of the present invention can modify circuit implementation 100 to include transistor 210, body contact 220, and resistor 230, as illustrated by the circuit implementation 200 shown in FIGURE 2. Source 213 and gate 215 of transistor 210 can be connected to final stage 110 and WL 120, respectively. Drain 217 of transistor 210 can connect to resistor 230 through body contact 220. Transistor 210 is coupled to body contact 220 which is connected to substrate wells 135 and 145 of memory cells 130 and 140. In some exemplary embodiments, a body contact, such as 220, can be connected to the substrate wells of all array devices connected to a word line, such as WL 120. In the exemplary embodiment illustrated in FIGURE 2, if WL 120 is inactive, body contact 220 will be connected to a fixed potential of -0.5 volts via resistor 230. Once WL 120 is activated, the potential at body contact 220 will be adjusted to 0 volts as long as the on-resistance of transistor switch 210 is considerably lower (e.g., 5-10.times. lower) than the resistance of resistor 230. This can result in reduced body effect and improved array device performance while WL 120 is activated.